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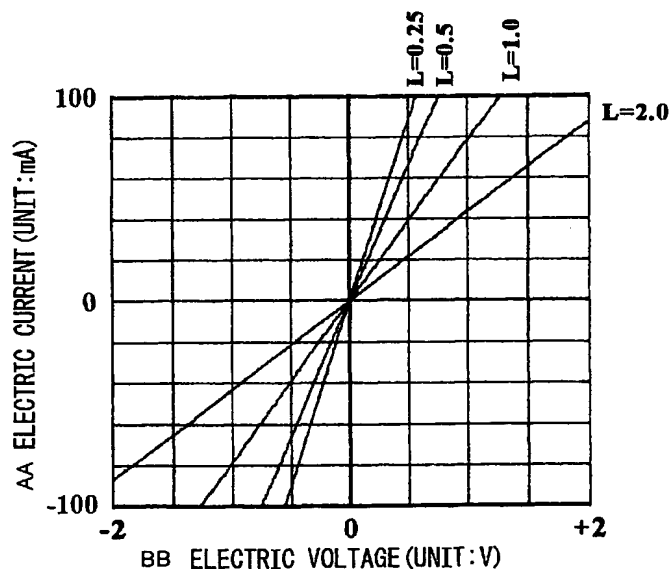
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(54) Title: **n-TYPE OHMIC ELECTRODE FOR n-TYPE GROUP III NITRIDE SEMICONDUCTOR, SEMICONDUCTOR LIGHT-EMITTING DEVICE WITH THE ELECTRODE, AND METHOD FOR FORMING n-TYPE OHMIC ELECTRODE**



(57) Abstract: The present invention provides a constitution of n-type ohmic electrode suitable for n-type group III nitride semiconductor, and a forming method thereof for providing low contact resistivity. The n-type ohmic electrode is provided to comprise an alloy of aluminum and lanthanum or comprises lanthanum at the junction interface with the n-type group III nitride semiconductor. The method comprising forming a lanthanum-aluminum alloy layer at 300°C or less to form an n-type ohmic electrode enriched in lanthanum at the junction interface.

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